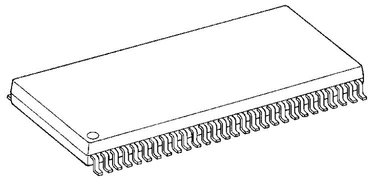
TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74VCXR162543FT

LOW-VOLTAGE 16-BIT REGISTERED TRANSCEIVER WITH 3.6 V TOLERANT INPUTS AND OUTPUTS

The TC74VCXR162543FT is a high performance CMOS 16-bit REGISTERED TRANSCEIVER. Designed for use in 1.8, 2.5 or 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.
It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.
The TC74VCXR162543FT can be used as two 8-bit transceivers or one 16-bit transceiver. Separate latch-enable ($\overline{LEAB}$ or $\overline{LEBA}$) and output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) inputs are provided for each register to permit independent control in either direction of data flow.
The A-to-B enable ($\overline{CEAB}$) input must be low in order to enter data from A or to output data from B. If $\overline{CEAB}$ is low and $\overline{LEAB}$ is low, the A-to-B latches are transparent; a subsequent low-to-high transition of $\overline{LEAB}$ puts the Alatches in the storage mode. With $\overline{CEAB}$ and $\overline{OEAB}$ both low, the 3 – state B outputs are active and reflect the data present at the output of the A latches. Data flow from B to A is similar but requires using the $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$ inputs.
When the $\overline{OE}$ input is high, the outputs are in a high impedance state. This device is designed to be used with 3 – state memory address drivers, etc.
The 26-Ω series resistor helps reducing output overshoot and undershoot without external resistor.
All inputs are equipped with protection circuits against static discharge.



TSSOP56-P-0061-0.50

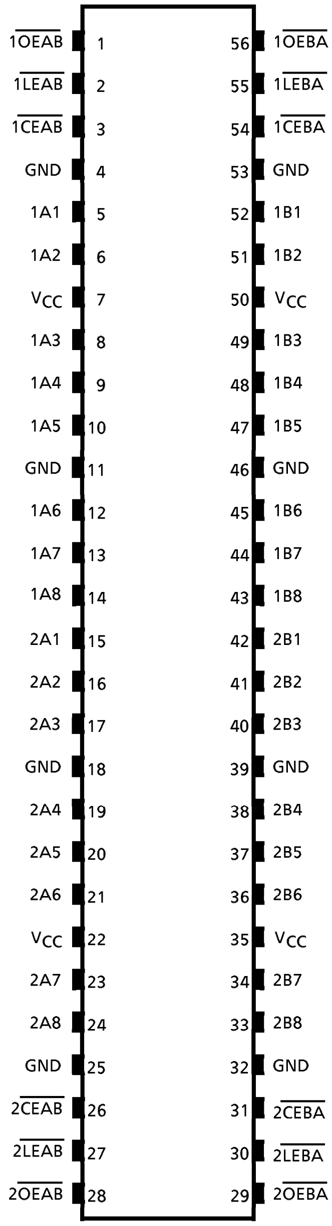
Weight : 0.25 g (Typ.)

FEATURES

- 26-Ω Series Resistors on Outputs.
- Low Voltage Operation : V_{CC} = 1.8~3.6 V
- High Speed Operation : t_{pd} = 4.4 ns (max) at V_{CC} = 3.0~3.6 V
  : t_{pd} = 5.4 ns (max) at V_{CC} = 2.3~2.7 V
  : t_{pd} = 9.8 ns (max) at V_{CC} = 1.8 V
- 3.6 V Tolerant inputs and outputs.
- Output Current : I_{OH} / I_{OL} = ±12 mA (min) at V_{CC} = 3.0 V
  : I_{OH} / I_{OL} = ±8 mA (min) at V_{CC} = 2.3 V
  : I_{OH} / I_{OL} = ±4 mA (min) at V_{CC} = 1.8 V
- Latch-up Performance : ±300 mA
- ESD Performance : Human Body Model > ±2000 V
  : Machine Model > ±200 V
- Package : TSSOP
  (Thin Shrink Small Outline Package)
- Power Down Protection is provided on all inputs and outputs.
- Supports live insertion / withdrawal (Note 3).

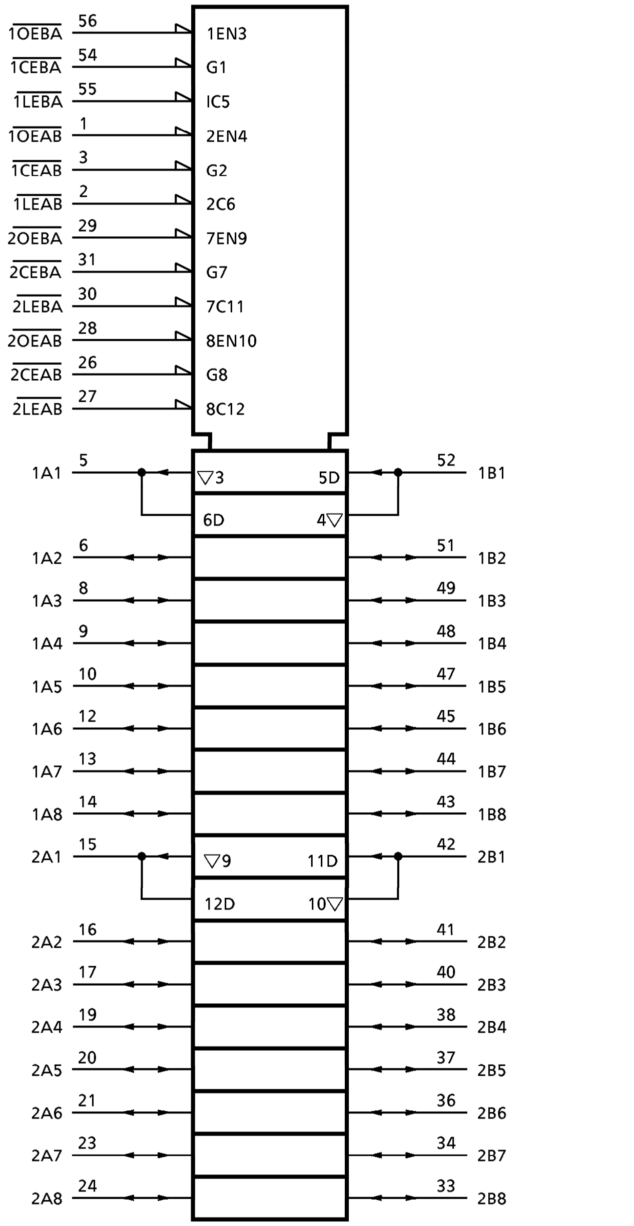
(Note 1) : Do not apply a signal to any bus terminal when it is in the output mode. Damage may result.
(Note 2) : All floating (high impedance) bus terminal must have their input level fixed by means of pull up or pull down resistors.
(Note 3) : To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

PIN ASSIGNMENT



(TOP VIEW)

SYMBOL



980910EBA2'

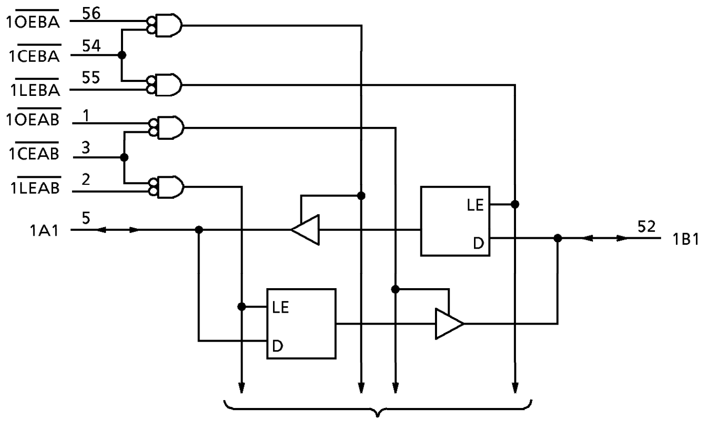
FUNCTION TABLE* (each 8-bit latch)

INPUTS				OUTPUTS
$\overline{CEAB}$	$\overline{LEAB}$	$\overline{OEAB}$	A	B
H	X	X	X	Z
X	X	H	X	Z
L	H	L	X	B_0**
L	L	L	L	L
L	L	L	H	H

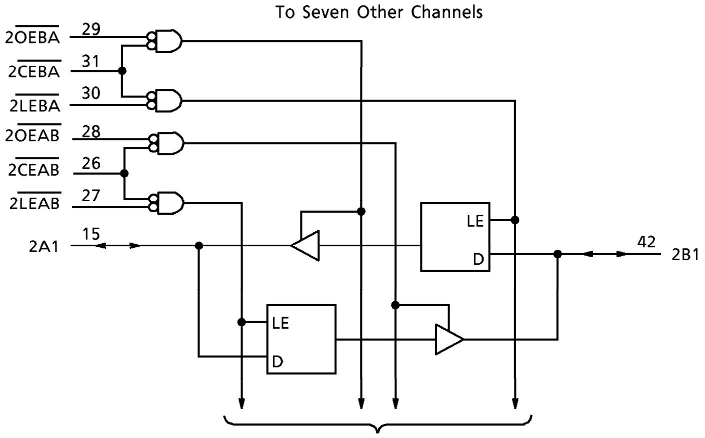
* A-to-B data flow is shown; B-to-A flow control is the same except that it uses $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.

** Output level before the indicated steady-state input conditions were established.

SYSTEM DIAGRAM



To Seven Other Channels



To Seven Other Channels

MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	V_{CC}	−0.5~4.6	V
DC Input Voltage ($\overline{OEAB}$, $\overline{OEBA}$, $\overline{LEAB}$, $\overline{LEBA}$, $\overline{CEAB}$, $\overline{CEBA}$)	V_{IN}	−0.5~4.6	V
DC Bus I/O Voltage	$V_{I/O}$	−0.5~4.6 (Note 1)	V
		−0.5~V_{CC} + 0.5 (Note 2)	
Input Diode Current	I_{IK}	−50	mA
Output Diode Current	I_{OK}	±50 (Note 3)	mA
DC Output Current	I_{OUT}	±50	mA
Power Dissipation	P_D	400	mW
DC V_{CC}/Ground Current Per Supply Pin	I_{CC}/I_{GND}	±100	mA
Storage Temperature	T_{stg}	−65~150	°C

(Note 1) : Off-State
(Note 2) : High or Low State. I_{OUT} absolute maximum rating must be observed.
(Note 3) : $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

RECOMMENDED OPERATING RANGE

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	1.8~3.6	V
		1.2~3.6 (Note 4)	
Input Voltage ($\overline{OEAB}$, $\overline{OEBA}$, $\overline{LEAB}$, $\overline{LEBA}$, $\overline{CEAB}$, $\overline{CEBA}$)	V_{IN}	−0.3~3.6	V
Bus I/O Voltage	$V_{I/O}$	0~3.6 (Note 5)	V
		0~V_{CC} (Note 6)	
Output Current	I_{OH}/I_{OL}	±12 (Note 7)	mA
		±8 (Note 8)	
		±4 (Note 9)	
Operating Temperature	T_{opr}	−40~85	°C
Input Rise And Fall Time	dt/dv	0~10 (Note 10)	ns/V

(Note 4) : Data Retention Only
(Note 5) : Off-State
(Note 6) : High or Low State
(Note 7) : V_{CC} = 3.0~3.6 V
(Note 8) : V_{CC} = 2.3~2.7 V
(Note 9) : V_{CC} = 1.8 V
(Note 10) : V_{IN} = 0.8~2.0 V, V_{CC} = 3.0 V

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = −40~85°C, 2.7 V < V_{CC} ≦ 3.6 V)

PARAMETER		SYMBOL	TEST CONDITION		V_{CC} (V)	MIN	MAX	UNIT
Input Voltage	"H" Level	V_{IH}			2.7~3.6	2.0	—	V
	"L" Level	V_{IL}			2.7~3.6	—	0.8	V
Output Voltage	"H" Level	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −100 μA	2.7~3.6	V_{CC} − 0.2	—	V
				I_{OH} = −6 mA	2.7	2.2	—	
				I_{OH} = −8 mA	3.0	2.4	—	
				I_{OH} = −12 mA	3.0	2.2	—	
	"L" Level	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA	2.7~3.6	—	0.2	V
				I_{OL} = 6 mA	2.7	—	0.4	
				I_{OL} = 8 mA	3.0	—	0.55	
				I_{OL} = 12 mA	3.0	—	0.8	
Input Leakage Current		I_{IN}	V_{IN} = 0~3.6 V		2.7~3.6	—	±5.0	μA
3-State Output Off-State Current		I_{OZ}	V_{IN} = V_{IH} or V_{IL} V_{OUT} = 0~3.6 V		2.7~3.6	—	±10.0	μA
Power Off Leakage Current		I_{OFF}	V_{IN}, V_{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent Supply Current		I_{CC}	V_{IN} = V_{CC} or GND		2.7~3.6	—	20.0	μA
			V_{CC} ≦ (V_{IN}, V_{OUT}) ≦ 3.6 V		2.7~3.6	—	±20.0	
Increase In I_{CC} Per Input		ΔI_{CC}	V_{IH} = V_{CC} − 0.6 V		2.7~3.6	—	750	μA

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = −40~85°C, 2.3 V ≦ V_{CC} ≦ 2.7 V)

PARAMETER		SYMBOL	TEST CONDITION		V_{CC} (V)	MIN	MAX	UNIT
Input Voltage	"H" Level	V_{IH}			2.3~2.7	1.6	—	V
	"L" Level	V_{IL}			2.3~2.7	—	0.7	V
Output Voltage	"H" Level	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −100 μA	2.3~2.7	V_{CC} − 0.2	—	V
				I_{OH} = −4 mA	2.3	2.0	—	
				I_{OH} = −6 mA	2.3	1.8	—	
				I_{OH} = −8 mA	2.3	1.7	—	
	"L" Level	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA	2.3~2.7	—	0.2	V
				I_{OL} = 6 mA	2.3	—	0.4	
				I_{OL} = 8 mA	2.3	—	0.6	
Input Leakage Current		I_{IN}	V_{IN} = 0~3.6 V		2.3~2.7	—	±5.0	μA
3-State Output Off-State Current		I_{OZ}	V_{IN} = V_{IH} or V_{IL} V_{OUT} = 0~3.6 V		2.3~2.7	—	±10.0	μA
Power Off Leakage Current		I_{OFF}	V_{IN}, V_{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent Supply Current		I_{CC}	V_{IN} = V_{CC} or GND		2.3~2.7	—	20.0	μA
			V_{CC} ≦ (V_{IN}, V_{OUT}) ≦ 3.6 V_{CC}		2.3~2.7	—	±20.0	

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = −40~85°C, 1.8 V ≦ V_{CC} < 2.3 V)

PARAMETER		SYMBOL	TEST CONDITION		V_{CC} (V)	MIN	MAX	UNIT
Input Voltage	"H" Level	V_{IH}			1.8~2.3	0.7 × V_{CC}	—	V
	"L" Level	V_{IL}			1.8~2.3	—	0.2 × V_{CC}	V
Output Voltage	"H" Level	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −100 μA	1.8	V_{CC} − 0.2	—	V
				I_{OH} = −4 mA	1.8	1.4	—	
	"L" Level	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA	1.8	—	0.2	V
				I_{OL} = 4 mA	1.8	—	0.3	
Input Leakage Current		I_{IN}	V_{IN} = 0~3.6 V		1.8	—	±5.0	μA
3-State Output Off-State Current		I_{OZ}	V_{IN} = V_{IH} or V_{IL} V_{OUT} = 0~3.6 V		1.8	—	±10.0	μA
Power Off Leakage Current		I_{OFF}	V_{IN}, V_{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent Supply Current		I_{CC}	V_{IN} = V_{CC} or GND		1.8	—	20.0	μA
			V_{CC} ≦ (V_{IN}, V_{OUT}) ≦ 3.6 V		1.8	—	±20.0	

AC characteristics (Ta = −40~85°C, Input t_r = t_f = 2.0 ns, C_L = 30 pF, R_L = 500 Ω)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	MIN	MAX	UNIT
Propagation Delay Time (An, Bn-Bn, An)	t_{pLH} t_{pHL}	(Fig.1, 2)	1.8	1.5	9.8	MHz
			2.5 ± 0.2	0.8	5.4	
			3.3 ± 0.3	0.6	4.4	
Propagation Delay Time ($\overline{LEAB}$, $\overline{LEBA}$-Bn, An)	t_{pLH} t_{pHL}	(Fig.1, 2)	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	6.4	
			3.3 ± 0.3	0.6	4.8	
3-State Output Enable Time ($\overline{OEAB}$, $\overline{OEBA}$, $\overline{CEAB}$, $\overline{CEBA}$)	t_{pZL} t_{pZH}	(Fig.1, 3)	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	5.9	
			3.3 ± 0.3	0.6	4.3	
3-State Output Disable Time ($\overline{OEAB}$, $\overline{OEBA}$, $\overline{CEAB}$, $\overline{CEBA}$)	t_{pLZ} t_{pHZ}	(Fig.1, 3)	1.8	1.5	8.8	ns
			2.5 ± 0.2	0.8	4.9	
			3.3 ± 0.3	0.6	4.3	
Minimum Pulse Width ($\overline{LEAB}$, $\overline{LEBA}$, $\overline{CEAB}$, $\overline{CEBA}$)	$t_{W (H)}$	(Fig.1, 2)	1.8	4.0	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum Set-up Time (An, Bn-$\overline{LE}$, $\overline{CE}$)	t_s	(Fig.1, 2)	1.8	2.5	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum Hold Time (An, Bn-$\overline{LE}$, $\overline{CE}$)	t_h	(Fig.1, 2)	1.8	1.0	—	ns
			2.5 ± 0.2	1.0	—	
			3.3 ± 0.3	1.0	—	
Output to Output Skew	t_{osLH} t_{osHL}	(Note 11)	1.8	—	0.5	ns
			2.5 ± 0.2	—	0.5	
			3.3 ± 0.3	—	0.5	

For C_L = 50 pF, add approximately 300 ps to the AC maximum specification.

(Note 11) : Parameter guaranteed by design.
($t_{osLH} = |t_{pLHm} - t_{pLHn}|$, $t_{osHL} = |t_{pHLm} - t_{pHLn}|$)

Dynamic switching characteristics (Ta = 25°C, Input t_r = t_f = 2.0 ns, C_L = 30 pF)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	TYP.	UNIT
Quiet Output Maximum Dynamic V_{OL}	V_{OLP}	V_{IH} = 1.8 V, V_{IL} = 0 V (Note 12)	1.8	0.15	V
		V_{IH} = 2.5 V, V_{IL} = 0 V (Note 12)	2.5	0.25	
		V_{IH} = 3.3 V, V_{IL} = 0 V (Note 12)	3.3	0.35	
Quiet Output Minimum Dynamic V_{OL}	V_{OLV}	V_{IH} = 1.8 V, V_{IL} = 0 V (Note 12)	1.8	−0.15	V
		V_{IH} = 2.5 V, V_{IL} = 0 V (Note 12)	2.5	−0.25	
		V_{IH} = 3.3 V, V_{IL} = 0 V (Note 12)	3.3	−0.35	
Quiet Output Minimum Dynamic V_{OH}	V_{OHV}	V_{IH} = 1.8 V, V_{IL} = 0 V (Note 12)	1.8	1.55	V
		V_{IH} = 2.5 V, V_{IL} = 0 V (Note 12)	2.5	2.05	
		V_{IH} = 3.3 V, V_{IL} = 0 V (Note 12)	3.3	2.65	

(Note 12) : Parameter guaranteed by design.

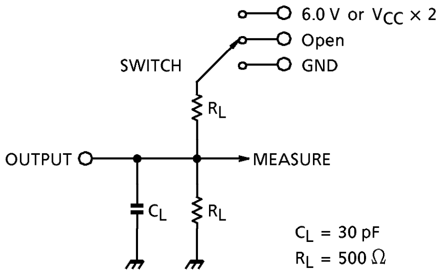
Capacitive characteristics (Ta = 25°C)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	TYP.	UNIT
Input Capacitance	C_{IN}	$\overline{OEAB}$, $\overline{OEBA}$, $\overline{CEAB}$, $\overline{CEBA}$, $\overline{LEAB}$, $\overline{LEBA}$	1.8, 2.5, 3.3	6	pF
Bus I/O Capacitance	$C_{I/O}$	—	1.8, 2.5, 3.3	7	pF
Power Dissipation Capacitance	C_{PD}	f_{IN} = 10 MHz (Note 13)	1.8, 2.5, 3.3	20	pF

(Note 13) : C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.
Average operating current can be obtained by the equation :
$I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 16$ (per bit)

TEST CIRCUIT

Fig.1



PARAMETER	SWITCH
t_{pLH}, t_{pHL}	Open
t_{pLZ}, t_{pZL}	6.0 V @V_{CC} = 3.3 ± 0.3 V V_{CC} × 2 @V_{CC} = 2.5 ± 0.2 V @V_{CC} = 1.8 V
t_{pHZ}, t_{pZH}	GND

AC WAVEFORM

Fig.2 t_{pLH}, t_{pHL}, t_w, t_s, t_h

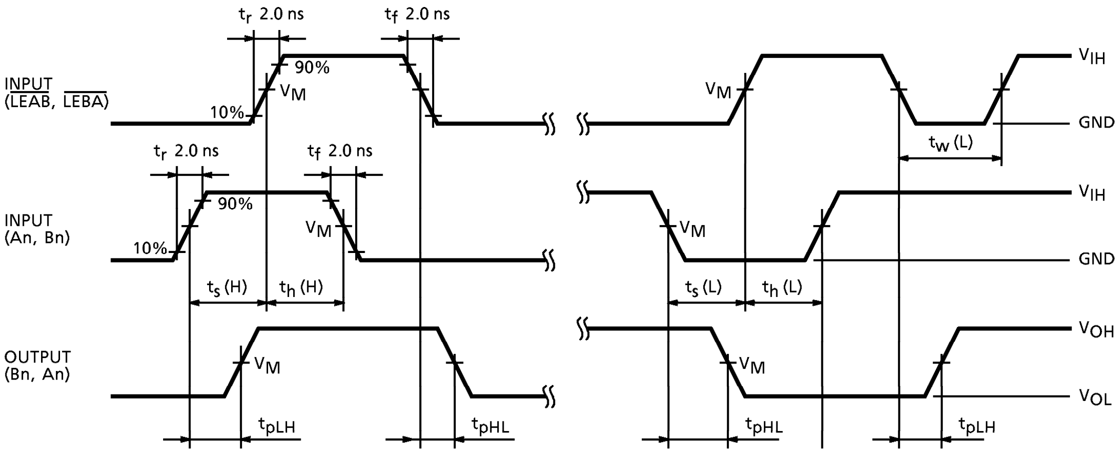


Fig.3 t_w, t_s, t_h

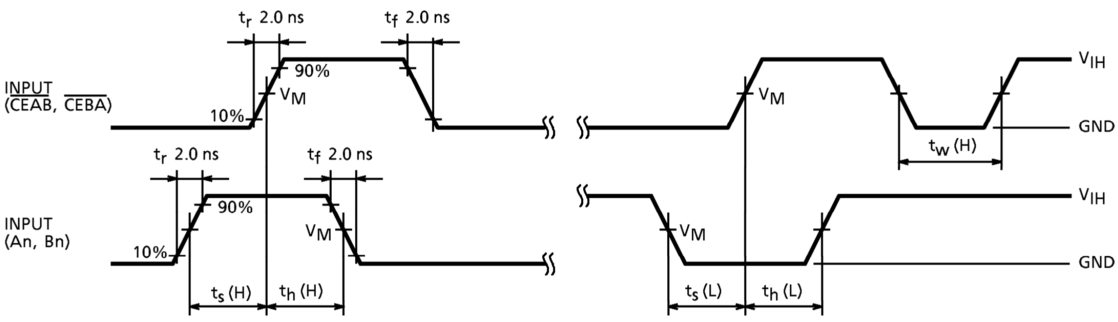
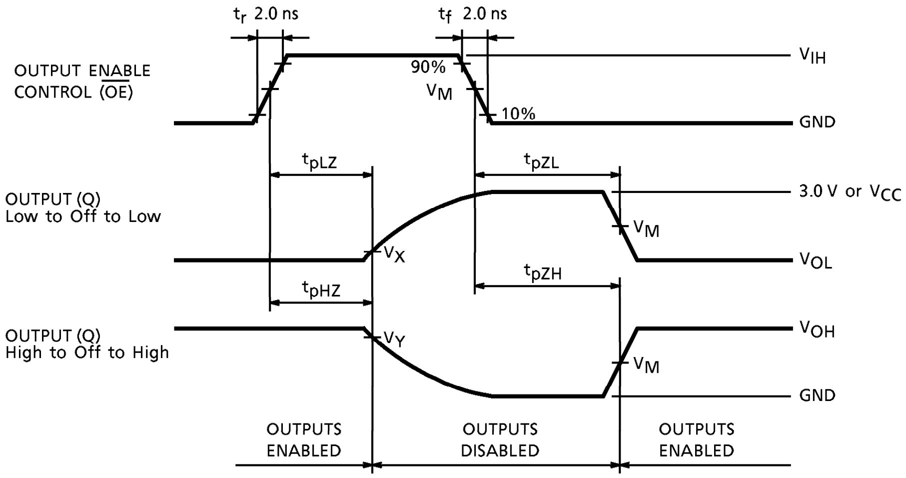


Fig.4 t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}

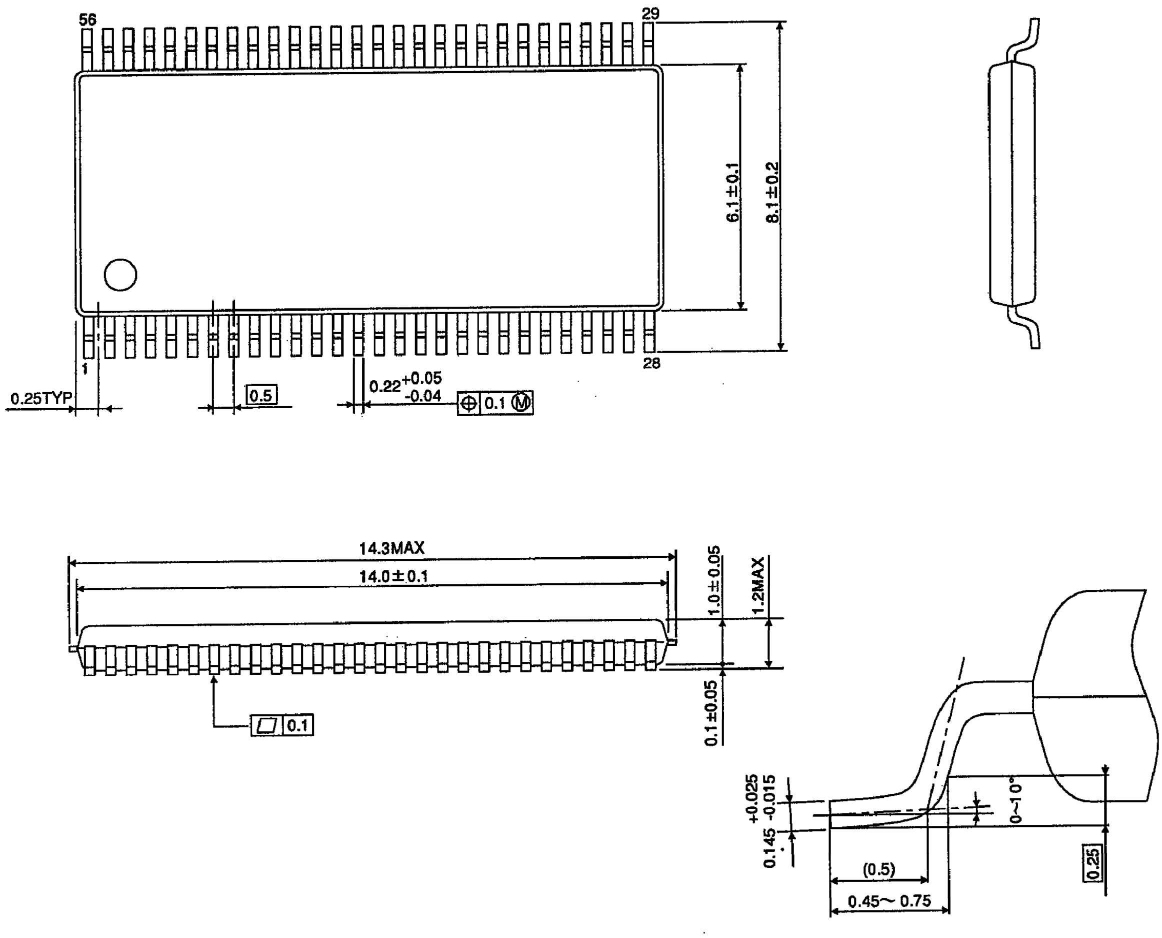


SYMBOL	V_{CC}		
	3.3 ± 0.3V	2.5 ± 0.2 V	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	V_{CC} / 2	V_{CC} / 2
V_X	V_{OL} + 0.3 V	V_{OL} + 0.15 V	V_{OL} + 0.15 V
V_Y	V_{OH} − 0.3 V	V_{OH} − 0.15 V	V_{OH} − 0.15 V

OUTLINE DRAWING

TSSOP56-P-0061-0.50

Unit : mm



Weight : 0.25 g (Typ.)